



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
30V	2.8Ω @ V _{GS} = 10V	380mA
307	3.8Ω @ $V_{GS} = 5V$	330mA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

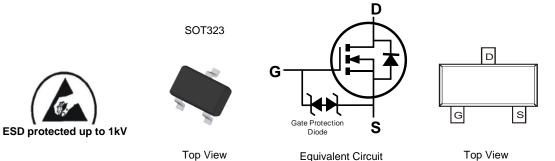
- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 1kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42
 Leadframe. Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.006 grams (Approximate)



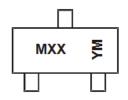
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN63D8LW-7	SOT323	3000/Tape & Reel
DMN63D8LW-13	SOT323	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



MXX= Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Date Code it	.Cy											
Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	E	F	G	Н	ı	J	K	L	M
NA (1-		F-1						A	0	0-1		D
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Prain Correct (Nata C) V	$T_A = +25$ °C $T_A = +70$ °C	I _D	380 300	mA	
Continuous Drain Current (Note 6) V _{GS} = 10V	t<5s	I _D	430 340	mA	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	%) (Note 6)	I _{DM}	1.2	Α	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	426	°C/W
Total Power Dissipation (Note 6)		P_{D}	420	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	301	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

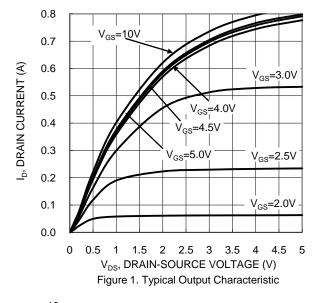
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	1		1	1			
Drain-Source Breakdown Voltage	BV _{DSS}	30		—	V	V _{GS} = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 30V$, $V_{GS} = 0V$	
Gate-Source Leakage	I_{GSS}	_	_	±10.0	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	8.0	_	1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
				2.8		$V_{GS} = 10.0V, I_D = 250mA$	
			_	3.8		$V_{GS} = 5.0V, I_D = 250mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}		_	4.2	Ω	$V_{GS} = 4.5V, I_D = 250mA$	
			_	4.5		$V_{GS} = 4.0V, I_D = 250mA$	
			_	13		$V_{GS} = 2.5V, I_D = 10mA$	
Forward Transconductance	g FS	80		_	mS	V _{DS} = 10V, I _D = 0.115A	
Diode Forward Voltage	V _{SD}		8.0	1.2	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		23.2	_			
Output Capacitance	Coss		3.0	_	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C _{rss}	_	2.2	_			
Gate Resistance	R _G		79.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge V _{GS} = 10V	Qg	_	0.9	_			
Total Gate Charge V _{GS} = 4.5V	Qg	_	0.4	_	nC	$V_{GS} = 10V, V_{DS} = 30V,$	
Gate-Source Charge	Q _{gs}		0.1	_	ПС	$I_D = 150 \text{mA}$	
Gate-Drain Charge	Q _{gd}	_	0.2	_			
Turn-On Delay Time	t _{D(ON)}		2.3	_			
Turn-On Rise Time	t _R	_	3.9	_	ĺ	$V_{DD} = 30V, I_D = 0.115A, V_{GEN} = 10V.$	
Turn-Off Delay Time	t _{D(OFF)}		11.4	_	ns	$R_{GEN} = 25\Omega$	
Turn-Off Fall Time	t _F		16.7	_			

5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

- Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.





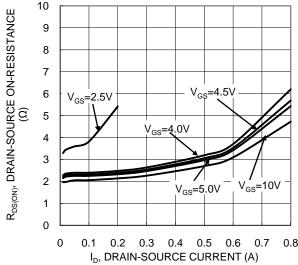


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

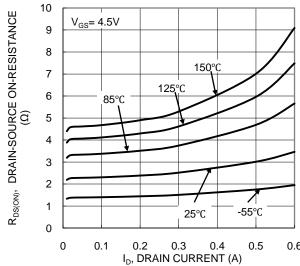
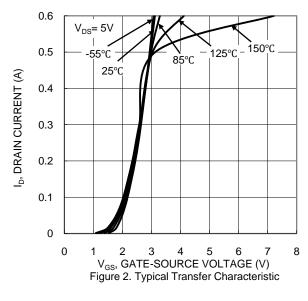
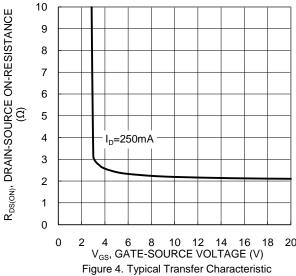
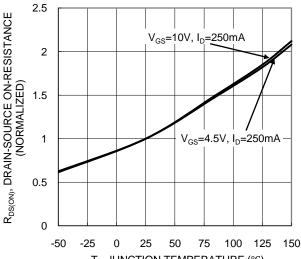


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature







T_J, JUNCTION TEMPERATURE (°C) Figure 6. On-Resistance Variation with Junction Temperature



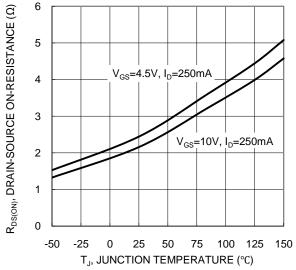
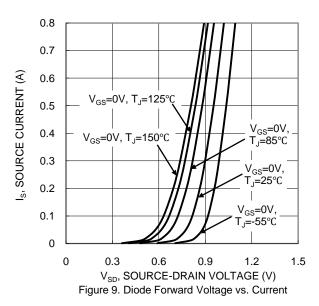


Figure 7. On-Resistance Variation with Junction Temperature



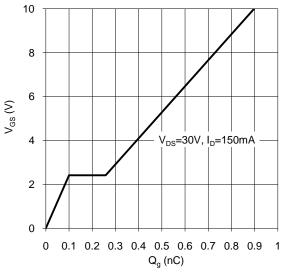


Figure 11. Gate Charge

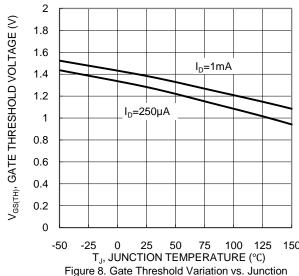
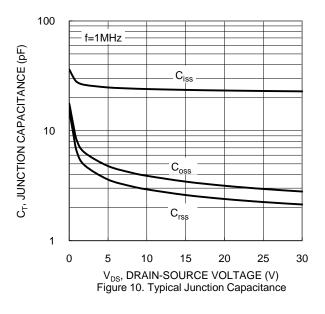
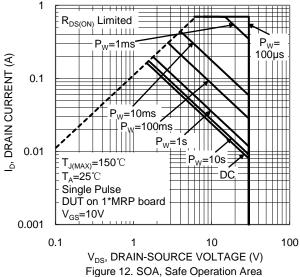


Figure 8. Gate Threshold Variation vs. Junction Temperature







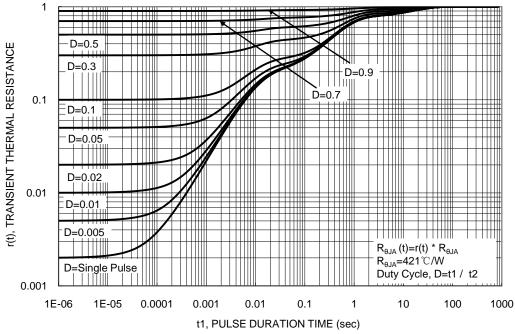
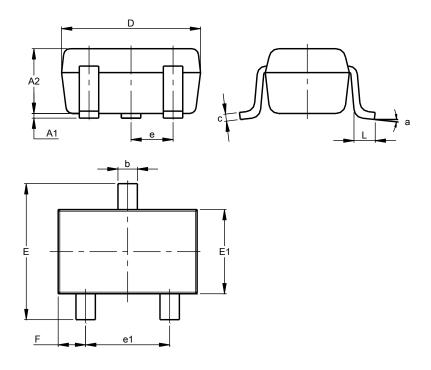


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

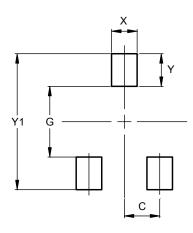


	SOT323								
Dim	Min	Max	Тур						
A1	0.00	0.10	0.05						
A2	0.90	1.00	0.95						
b	0.25	0.40	0.30						
С	0.10	0.18	0.11						
D	1.80	2.20	2.15						
Е	2.00	2.20	2.10						
E1	1.15	1.35	1.30						
е	().650 E	SC						
e1	1.20	1.40	1.30						
F	0.375	0.475	0.425						
L	0.25	0.40	0.30						
а	8°								
All	All Dimensions in mm								



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	0.650			
G	1.300			
Х	0.470			
Y	0.600			
Y1	2.500			

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